

Features

- Blocking voltage to 800 V
- RMS on-state current to 1 A
- General purpose bidirectional switching

ANODE
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3. GATE



Package Marking and Ordering Information

Product ID	Pack	Packing Method	Qty(PCS)	
BT131-800D	SOT-89	Tape and Reel	3000	



Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Value	Unit	
V _{DRM} /V _{RRM}	repetitive peak off-state voltage		800	V	
I _{T(RMS)}	RMS on-state current		1	Α	
1	Non repetitive surge peak	t = 20ms T _j = 25°C	10	_	
I _{TSM}	on-state current	t = 16.7ms T _j = 25°C	8	A	
l ² t	I ² t for fusing	t = 10 ms	1	A ² s	
dl/dt	Critical-rate of rise of I II III commutation current IV	I _G =2I _{GT} tr≤100ns F=120Hz	50 10	A/us	
I _{GM}	Peak Gate Current	T _j =125°C tp=20µs	0.3	Α	
V _{GM}	Peak gate voltage	T _j =125 °C	1	V	
P _{GM}	Peak gate power	T _j =125 °C	0.8	W	
P _{G(AV)}	Average Gate Power Dissipation	T _j =125 °C	0.4	W	
T _j	Junction Temperature	-	-40 ~ 125	°C	
T _{stg}	Storage Temperature	-	-40 ~ 150	°C	

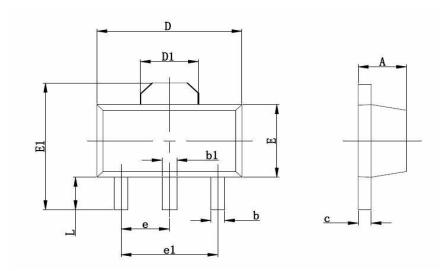


Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter		Symbol	Test conditions		Min	Тур	Max	Unit
Repetitive Peak Off-State Current		I _{DRM,} I _{RRM}	V _{DRM} =V _{RRM} T _j =25°C				5	μΑ
Repetitive Peak Reverse Current		Draw, raaw	$V_{DRM} = V_{RRM} T_j = 125 °C$				1	mA
Gate non-trigger voltage		V_{GD}	$V_D = 1/2V_{DRM}$		0.2			V
On-state voltage		V_{TM}	I _T =0.8A,t _p =380us				1.65	V
	I	I _{GT}	T ₂ (+), G(+)	V _D =12V			3	mA
Gate trigger current	Ш		T ₂ (+), G(-)				6	
Gate trigger current	III		T ₂ (-), G(-)	R _L =100Ω			4	
	IV		T ₂ (-), G(+)				8	
	I	V _{GT}	T ₂ (+), G(+)			8.0	2	V
Gate trigger voltage	II		T ₂ (+), G(-)	V _D =12V		8.0	2	
Gate trigger voltage	III		T ₂ (-), G(-)	R _L =100Ω		0.8	2	
	IV		T ₂ (-), G(+)			8.0	2.5	
Holding current		l _Η	V _D =12V ,I _{GT} =100mA				30	mA
Critical-rate of rise of commutation		dV/dt	V _{DM} =67%V _{DRM}				50	V/us
voltage			Gate open T _j =125 °C					
Rate of change of commutating voltage		(dl/dt)c	V _{DM} =400V T _j =125 °C				20	V/us
			(dl/dt)c=5.4A/ms Gate open					
Turn-on time		t _{gt}	I _{TM} =16A ,V _{DM} =V _{DRM(MAX)} I _G =0.1A,dI _G dt=5A uS				2	us



SOT-89 Package Outline Dimensions



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF.		0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	



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